

AMENDMENTS TO THE CLAIMS

1-33. (Canceled)

34. (Currently Amended) A plating method comprising:

preparing a substrate having fine recesses for interconnects covered with a seed layer;
supplying a plating solution between a surface of the seed layer and an anode spaced from the seed layer at a certain interval through a porous contact member; and

plating the substrate by applying plating voltage between the seed layer and said anode while intermittently stopping the plating by applying no voltage between the seed layer and said anode for supplying a new plating solution between the seed layer and said porous contact member;

wherein said plating is performed while a change of state of the plating voltage that is applied between the seed layer and the anode occurs that results from intermittence of the plating voltage, a change of pressing state between said porous contact member and the seed layer occurs, and the change of state of the plating voltage is correlated with the change of pressing state between said porous contact member and the seed layer.

35. (Original) A plating method according to claim 34, wherein said change of pressing state between said porous contact member and the seed layer is a change of pressure between said porous contact member and the seed layer.

36. (Canceled)

37. (Previously Presented) A plating method according to claim 34, wherein said change of the state of plating voltage applied between the seed layer and said anode, and said change of pressing state between said porous contact member and the seed layer, are correlated by applying said plating voltage when a pressure between said porous contact member and the surface of the seed layer is increased relative to a previous pressure, and by not applying said plating voltage when a pressure between said porous contact member and the seed layer is lowered relative to a previous pressure.

38. (Original) A plating method according to claim 34, wherein said change of pressing state between said porous contact member and the seed layer is a change of contact and non-contact between said porous contact member and the surface of the seed layer.

39. (Currently Amended) A plating method according to claim 34, wherein said change of the state of plating voltage applied between the seed layer and said anode, and said change of pressing state between said porous contact member and the seed layer, are correlated so as to synchronize contact between said porous contact member and the surface of the seed layer and application of plating voltage between the seed layer and said anode.

40. (Previously Presented) A plating method according to claim 34, wherein said change of the state of plating voltage applied between the seed layer and said anode, and said change of pressing state between said porous contact member and the seed layer, are correlated so as not to apply plating voltage between the seed layer and said anode when said porous contact member is brought out of contact with the surface of the seed layer, and so as to apply plating voltage between the seed layer and said anode after an elapse of a certain period of time after said porous contact member is brought into contact with the surface of the seed layer.

41-58. (Canceled)